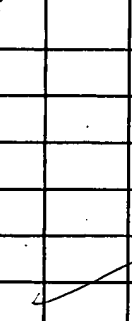


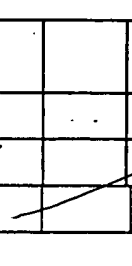
U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				SNDK.310US0		10/600,259	
				Applicant(s)			
(Use several sheets if necessary)				Filing Date		Group	
				06/20/03		Unknown	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.							


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Jeffrey Lutze et al.		Filing Date			
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Unknown					



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